

Dual N-Channel 2.5-V (G-S) MOSFET

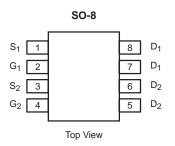
PRODUCT SUMMARY				
V _{DS} (V)	$V_{DS}(V)$ $R_{DS(on)}(\Omega)$			
20	0.022 at $V_{GS} = 4.5 \text{ V}$	6.6		
	$0.030 \text{ at V}_{GS} = 2.5 \text{ V}$	5.5		

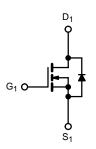
FEATURES

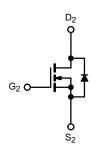
- Halogen-free Option Available
- TrenchFET® Power MOSFETs



RoHS³







N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	20		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Desir Courset /T 450 90\8	T _A = 25 °C	- I _D	6.6	5.2		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		5.5	3.5	۸	
Pulsed Drain Current		I _{DM}	30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	1.5	1.0		
Mariana Barra Birata di ad	T _A = 25 °C	D.	1.5	1.0	W	
Maximum Power Dissipation ^a	T _A = 70 °C	- P _D	0.96	0.64	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Manifester Locality to Assistantia	t ≤ 10 s	R _{thJA}	72	83	
Maximum Junction-to-Ambient ^a	Steady State	' thJA	100	120	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	55	70	

Notes:

a. Surface Mounted on FR4 board, $t \le 10 \text{ s.}$

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

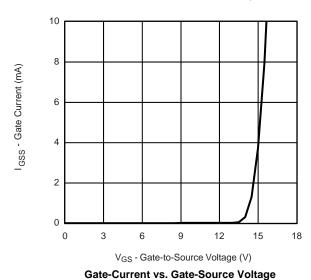


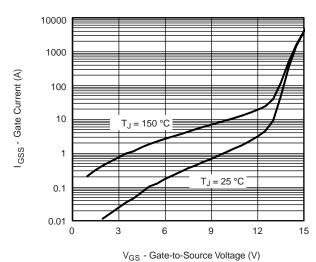
SPECIFICATIONS $T_J = 25 ^{\circ}C$, unless otherwise noted							
Parameter	Symbol	Test Conditions N		Typ. ^a	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.6		1.6	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA	
- 0.11 1.0	١.	V _{DS} = 20 V, V _{GS} = 0 V		1			
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 20 V, V _{GS} = 0 V, T _J = 70 °C			25	μΑ	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
5 1 0 0 0 1 1 b	В	$V_{GS} = 4.5 \text{ V}, I_D = 6.5 \text{ A}$		0.0165	0.022	0.022 0.030 Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 5.5 \text{ A}$		0.023	0.030		
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 10 \text{ V}, I_{D} = 6.5 \text{ A}$		30		S	
Diode Forward Voltage ^b	V_{SD}	I _S = 1.5 A, V _{GS} = 0 V		0.71	1.2	V	
Dynamic ^a							
Total Gate Charge	Qg			12	18		
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.5 \text{ A}$		2.2		nC	
Gate-Drain Charge	Q_{gd}			3.6			
Turn-On Delay Time	t _{d(on)}			245	365		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		330	495		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		860	1300	ns	
Fall Time	t _f			510	765		

Notes

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

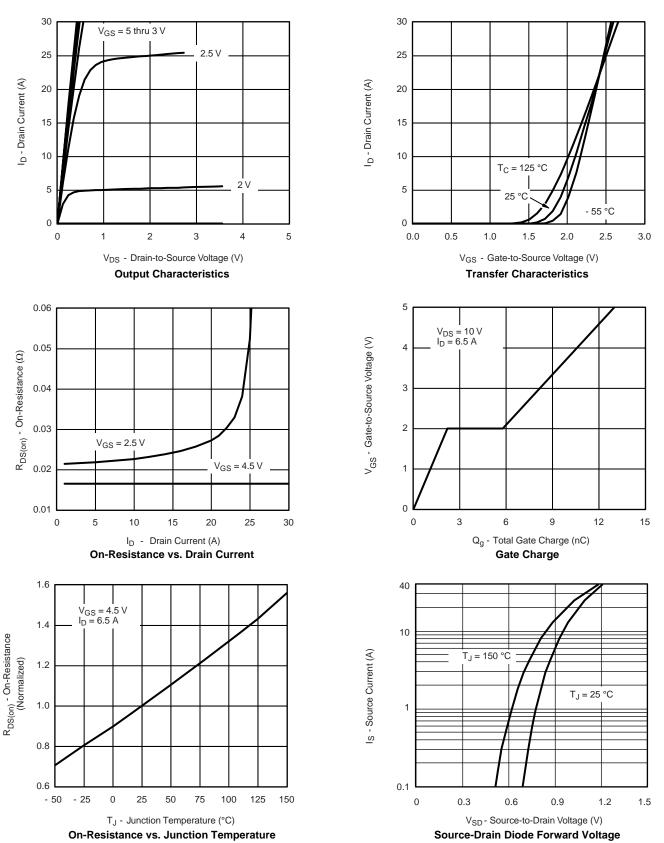
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





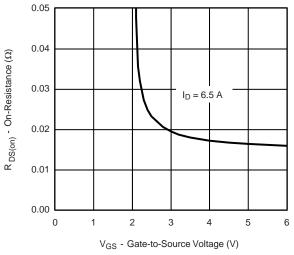
Gate Current vs. Gate-Source Voltage



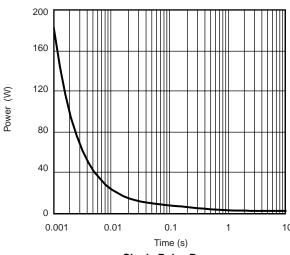




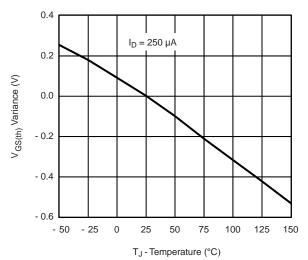




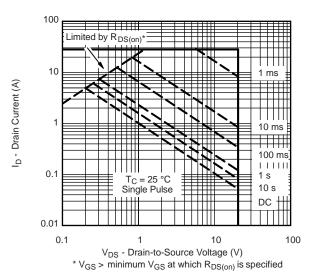
On-Resistance vs. Gate-to-Source Voltage



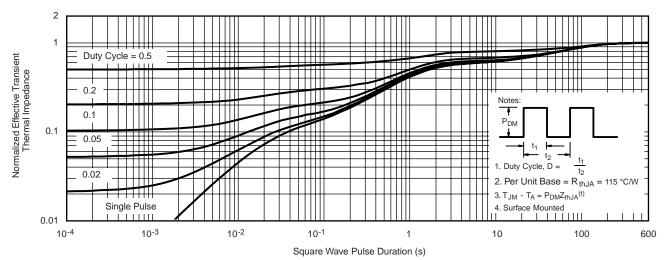
Single Pulse Power



Threshold Voltage



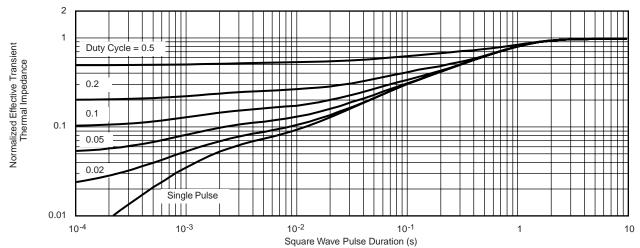
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient





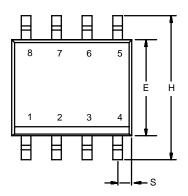


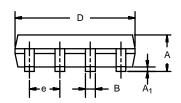
Normalized Thermal Transient Impedance, Junction-to-Foot

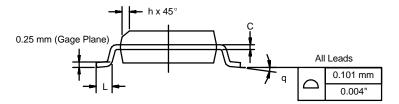




SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





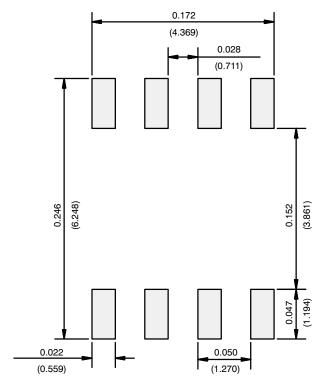


	MILLIM	IETERS	INC	HES	
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
FCN: C-06527-Rev I 11-Sen-06					

ECN: C-06527-Rev. I, 11-Sep-06

DWG: 5498

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index





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